

SUPPLEMENTARY EUROPEAN SEARCH REPORT

Application Number

EP 89 90 0040

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	DOCUMENTS CONSIDERE	D TO BE RELEVA	NT.	
Category	Citation of document with indication of relevant passages	where appropriate,	Relevant to claim	CLASSIFICATION OF THE APPLICATION (Int. Cl. 4)
Х	US-A-4 216 577 (BADET e * Figures 2-4; column 4, column 5, line 4; column *	line 62 -	1,2,5,9	H 01 L 23/48 H 01 L 29/52
X	FR-A-2 439 478 (HONEYWE * Figures 7-8; page 7, 1 8, line 38 *	LL-BULL) ine 34 - page	1-3,6,	
A ··	DE-A-3 222 791 (SIEMENS * Page 5, lines 16-19; po 16-19 *		6-8,14,	
A	EP-A-O 072 673 (3M) * Page 7, lines 13-15 *	:	4	
A	FR-A-2 205 800 (HONEYWE * Page 3, lines 15-33 *	LL-BULL)	1	
				TECHNICAL FIELDS SEARCHED (Int. Cl.4)
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	The supplementary search repoup for the claims attached here			
Place of search Date of completion of the search		0055	Examiner	
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X : par Y : par doc A : tec O : nor	CATEGORY OF CITED DOCUMENTS ticularly relevant if taken alone ticularly relevant if combined with another tument of the same category hnological background h-written disclosure ermediate document	E : earlier patent after the filing D : document cite L : document cite	d in the application d for other reasons	ished on, or

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CLAIMS

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What is claimed is:

1. A semiconductor device package comprising:

a tape including a patterned insulating layer and a conductive layer, said conductive layer being joined to said insulating layer;

a semiconductor die secured to one surface of said tape;

an insulating element joined to said conductive layer;

means for electrically coupling said semiconductor die to said conductive layer;

a body frame joined to said conductive layer and positioned about said semiconductor die and said electrical coupling means; and

an encapsulant body disposed over said frame and within said frame over said die and said electrical coupling means.

- 2. A semi-conductor device package as in Claim 1, including a conductive film disposed between said patterned insulating layer and said conductive layer.
- 3. A semiconductor device package as in Claim 2, wherein said conductive film is formed from sputtered copper.
- 30 4. A semiconductor device package as in Claim 1, wherein said insulating layer is made of a flexible material.
- A semiconductor device package as in Claim 3,
 wherein said insulating layer is made of Kapton.

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- 6. A semiconductor device package as in Claim 1, wherein said conductive layer is made of gold plate.
- 7. A semiconductor device package as in Claim 1, including an insulating element joined to the backside of said conductive layer.
 - 8. A semiconductor device package as in Claim 1, wherein said coupling means comprise bond wires.
 - 9. A semiconductor device package as in Claim 7, including a silicon gel disposed over said die and said bond wires.
- 10. A semiconductor device package as in Claim 1, including bond lead fingers coupled to said bond wires, and conductive pins coupled to said bond lead fingers for connection to external conductive leads.
- 20 11. A semiconductor device package as in Claim 1, wherein said electrical coupling means comprise conductive bumps.
- 12. A semiconductor device package as in Claim 10, wherein said insulating element is a backside element, and said body frame is connected to said backside element surrounding said conductive leads.
- 13. A semiconductor device package as in Claim 1, wherein said body frame has a height substantially greater than the thickness of said patterned insulating layer.
 - 14. A process of making a semiconductor device package comprising the steps of:

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forming a patterned wire bondable tape by sputtering a conductive film on an insulating layer;

etching the insulating layer and conductive film to define a pattern of conductive leads;

depositing a patterned conductive layer on said conductive film:

attaching a semiconductor die to said wire bondable tape;

forming electrical connections between said die and said conductive layer;

joining an insulating element to the backside of said conductive layer;

depositing a protective insulating coating over said die and electrical connections;

attaching a body frame to the upper surface of said conductive layer and insulating element, surrounding said die, electrical connections and coating; and

encapsulating said body frame, coating, die and electrical connections with an insulating material.

- 15. A process as in Claim 14, wherein said die is attached to said tape by a die attach epoxy and cured at a temperature of about 150°C for one hour or less.
- 16. A process as in Claim 14, including the step of forming said electrical connections are formed by thermosonically bonding wires between said die pads to conductive leads of said patterned conductive layer.
- 17. A process as in Claim 14, wherein said step of depositing a protective coating comprises applying a silicone gel to flow over said die and electrical connections and curing the gel coating.

18. A process as in Claim 14, including the step of causing a body frame adhesive to flow to said insulating element on said conductive leads.